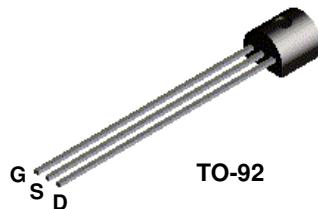




**Discrete POWER & Signal
Technologies**

**J201
J202**



**MMBFJ201
MMBFJ202**



N-Channel General Purpose Amplifier

This device is designed primarily for low level audio and general purpose applications with high impedance signal sources. Sourced from Process 52.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{DG}	Drain-Gate Voltage	40	V
V_{GS}	Gate-Source Voltage	- 40	V
I_{GF}	Forward Gate Current	50	mA
T_J, T_{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max		Units
		J201 / J202	*MMBFJ201	
P_D	Total Device Dissipation Derate above 25°C	625 5.0	350 2.8	mW mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	°C/W

* Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

N-Channel General Purpose Amplifier

(continued)

Electrical Characteristics

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units	
OFF CHARACTERISTICS						
$V_{(\text{BR})\text{GSS}}$	Gate-Source Breakdown Voltage	$I_G = -1.0 \mu\text{A}, V_{DS} = 0$	- 40		V	
I_{GSS}	Gate Reverse Current	$V_{GS} = -20 \text{ V}, V_{DS} = 0$		-100	pA	
$V_{GS(\text{off})}$	Gate-Source Cutoff Voltage	$V_{DS} = 20 \text{ V}, I_D = 10 \text{ nA}$	J201 J202	- 0.3 - 0.8	- 1.5 - 4.0	V

ON CHARACTERISTICS

I_{DSS}	Zero-Gate Voltage Drain Current*	$V_{DS} = 20 \text{ V}, I_{GS} = 0$	J201 J202	0.2 0.9	1.0 4.5	mA mA
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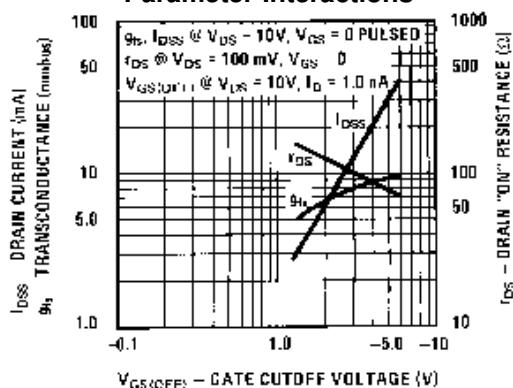
SMALL SIGNAL CHARACTERISTICS

y_{fs}	Forward Transfer Admittance	$V_{DS} = 20, f = 1.0 \text{ kHz}$	J201 J202	500 1000		μmhos μmhos
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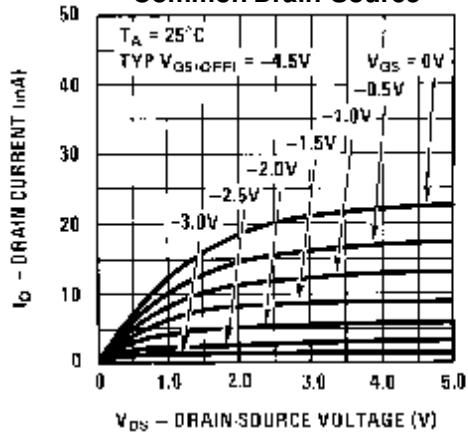
* Pulse Test: Pulse Width $\leq 300 \mu\text{s}$

Typical Characteristics

Parameter Interactions



Common Drain-Source

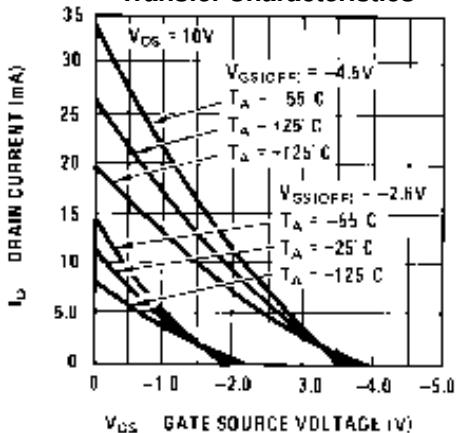


N-Channel General Purpose Amplifier

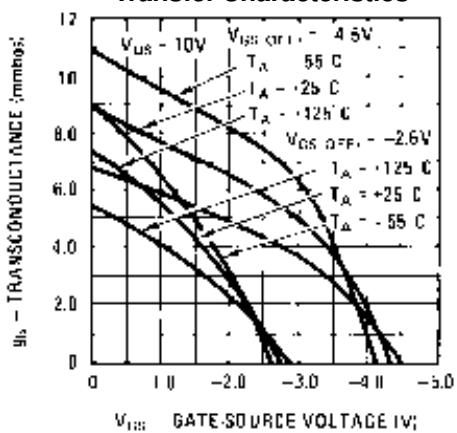
(continued)

Typical Characteristics (continued)

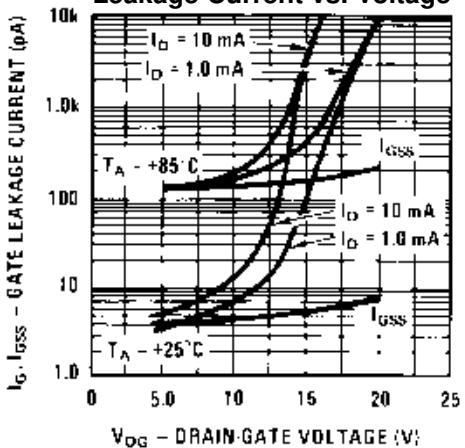
Transfer Characteristics



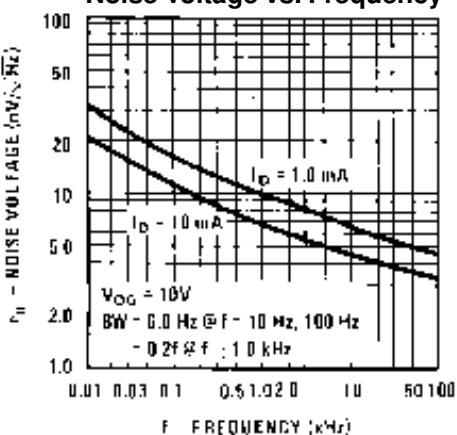
Transfer Characteristics



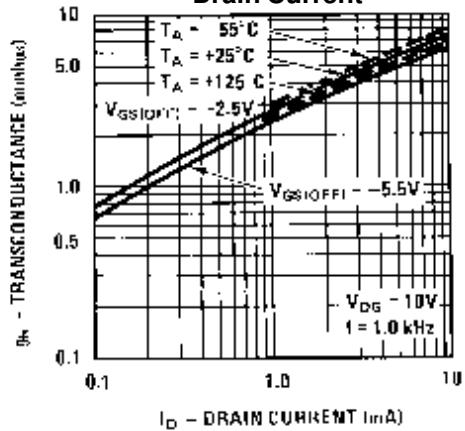
Leakage Current vs. Voltage



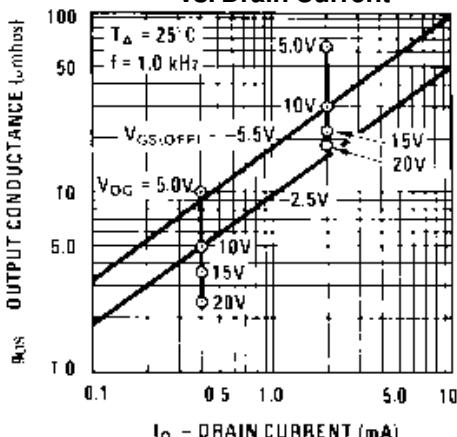
Noise Voltage vs. Frequency



Transconductance vs. Drain Current



Output Conductance vs. Drain Current

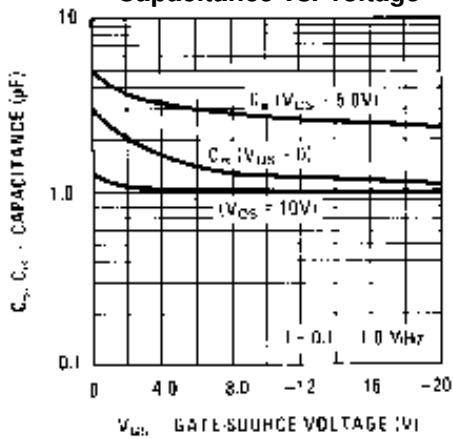


N-Channel General Purpose Amplifier

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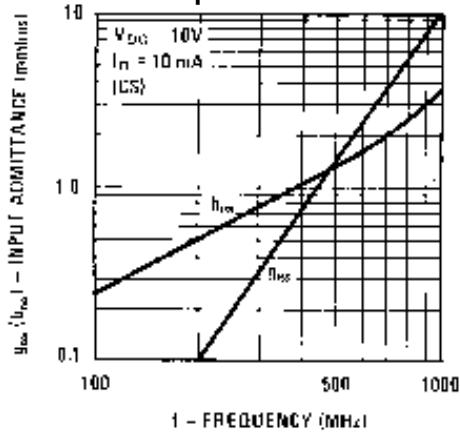
Typical Characteristics (continued)

Capacitance vs. Voltage

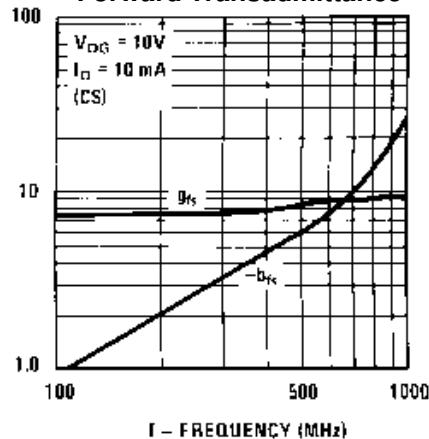


Common Source Characteristics

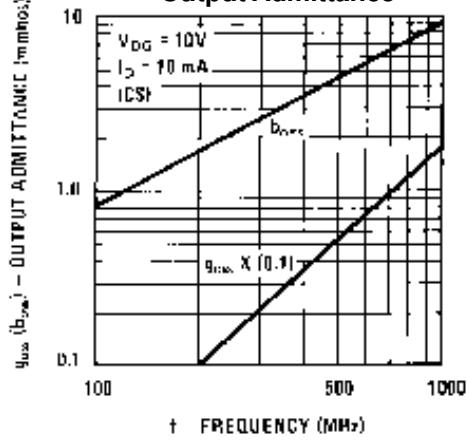
Input Admittance



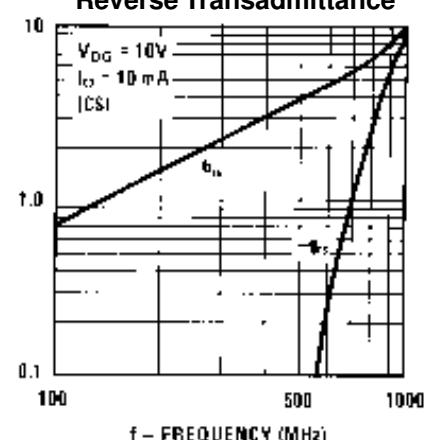
Forward Transadmittance



Output Admittance



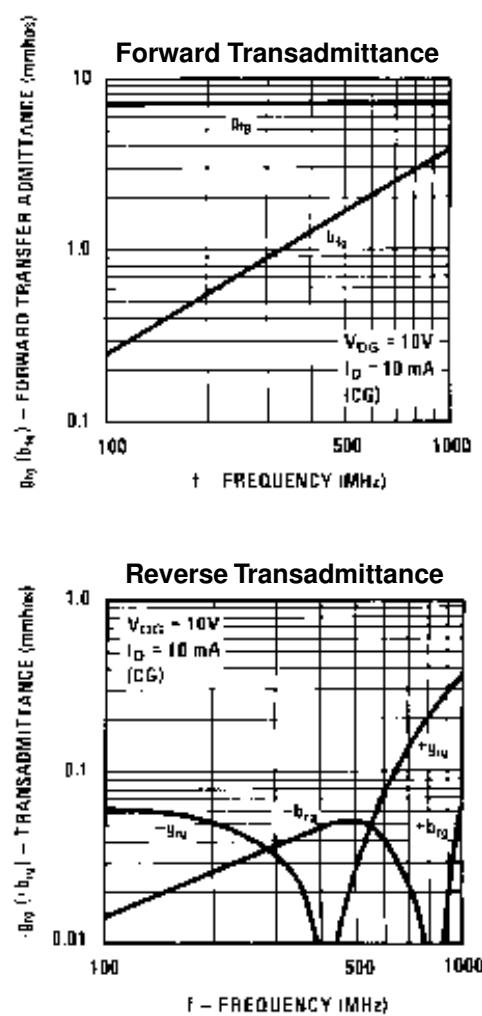
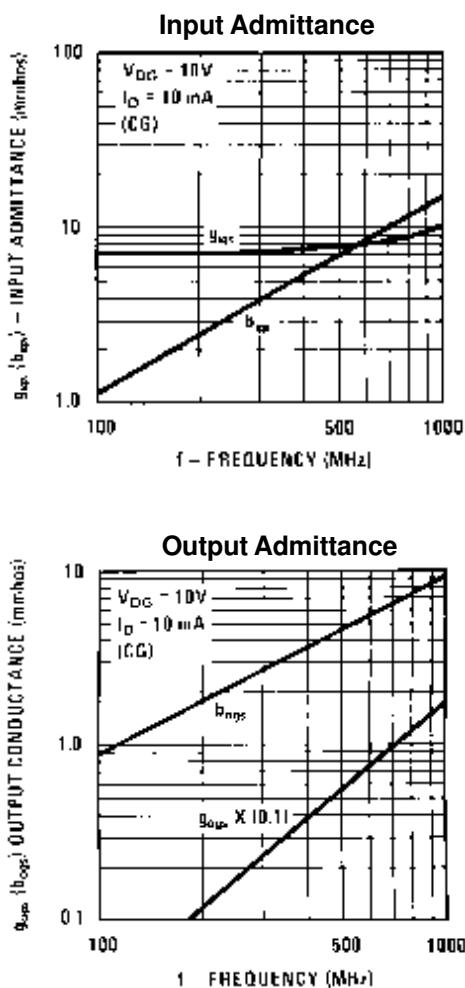
Reverse Transadmittance



N-Channel General Purpose Amplifier

• (continued)

Common Gate Characteristics



N-Channel General Purpose Amplifier
(continued)